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NTE6129 Silicon Power Rectifier Diode 700 Amp, DO200AB

Features:

- High Power, Fast Recovery Time
- High Current Capability
- Low Forward Recovery

Applications:

- Snubber Diode for GTO
- High Voltage Free-Wheeling Diode
- Fast Recovery Rectifier Applications

Ratings and Characteristics:

Average Forward Current ($T_C = +55^\circ\text{C}$ Max), $I_{F(AV)}$	700A
Maximum Repetitive Peak Reverse Voltage, V_{RRM}	1600V
Maximum Non-Repetitive Peak Reverse Voltage, V_{RSM}	1700V
Maximum Reverse Current ($T_J = +150^\circ\text{C}$), I_{RRM}	50mA
Maximum Forward Surge Current, I_{FSM} 50Hz	9300A
60Hz	9730A
Operating Junction Temperature Range, T_J	-40° to +150°C
Storage Temperature Range, T_{stg}	-40° to +150°C
Thermal Resistance, Junction-to-Case (DC Operation, single side cooled), R_{thJC}	0.092°C/W
Thermal Resistance, Case-to-Sink (DC Operation, double side cooled), R_{thCS}	0.46°C/W
Maximum Mounting Force ($\pm 10\%$), F	9800 (1000) N (Kg)

Electrical Specifications:

Parameter	Symbol	Test Conditions		Rating	Unit
Maximum Average Forward Current	$I_{F(AV)}$	180° condition, Half sine wave	Double side cooled, $T_C = +55^\circ\text{C}$	700	A
			Single side cooled, $T_C = +85^\circ\text{C}$	365	A

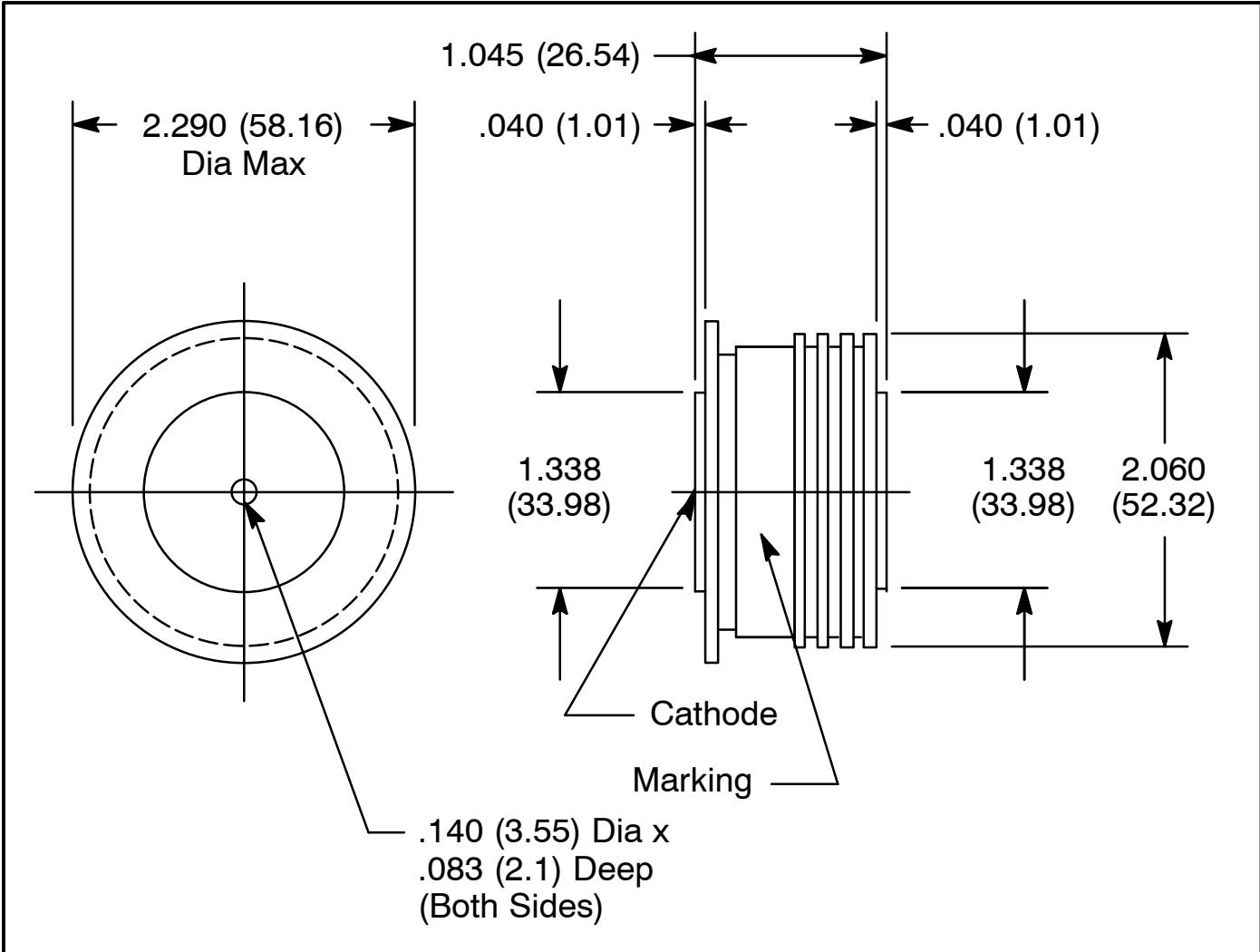
Parameter	Symbol	Test Conditions			Rating	Unit
Maximum RMS Forward Current	$I_{F(RMS)}$	@ +25°C heatsink temperature double side cooled			1320	A
Maximum Peak One-Cycle Non-Repetitive Surge Current	I_{FSM}	$t = 10\text{ms}$	Half sinewave current, rated V_{RRM} reapplied, initial $T_J = +150^\circ\text{C}$		7820	A
		$t = 8.3\text{ms}$			8190	A
		$t = 10\text{ms}$	Half sinewave current, no voltage reapplied, initial $T_J = +150^\circ\text{C}$		9300	A
		$t = 8.3\text{ms}$			7820	A

Electrical Specifications (Cont'd):

Parameter	Symbol	Test Conditions			Rating	Unit		
Maximum I^2t for Fusing	I^2t	$t = 10\text{ms}$	Rated V_{RRM} reapplied, initial $T_J = +150^\circ\text{C}$		306	A^2s		
		$t = 8.3\text{ms}$			279	A^2s		
		$t = 10\text{ms}$	No voltage reapplied, initial $T_J = +150^\circ\text{C}$		432	A^2s		
		$t = 8.3\text{ms}$			395	A^2s		
Maximum $I^2\sqrt{t}$	$I^2\sqrt{t}$	$t = 0.1 \text{ to } 10\text{ms}$, no voltage reapplied			4320	$\text{A}^2\sqrt{t}$		
Maximum Peak Forward Voltage	V_{FM}	$T_J = +150^\circ\text{C}$, $I_{pk} = 1500\text{A}$, $t_p = 10\text{ms}$			2.2	V		

Recovery Characteristics:

$T_J = +25^\circ\text{C}$ typical t_{rr} @ 25% I_{RRM}	Test Conditions			Max Values @ $T_J = +150^\circ\text{C}$		
	I_{pk} Square Pulse	di/dt	V_r	t_{rr} @ 25% I_{RRM}	Q_{rr}	T_{rr}
2.0 μs	1000A	50A/ μA	-50V	3.5 μs	240 μC	110A



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